DISCRETE SEMICONDUCTORS

DATA SHEET

PMBF4391; PMBF4392; PMBF4393

N-channel FETs

Product specification

April 1995



N-channel FETs

PMBF4391; PMBF4392; PMBF4393

DESCRIPTION

Symmetrical silicon n-channel depletion type junction field-effect transistors on a plastic microminiature envelope intended for application in thick and thin-film circuits. The transistors are intended for low-power chopper or switching applications in industry.

PINNING

1 = drain

2 = source

3 = gate

Note

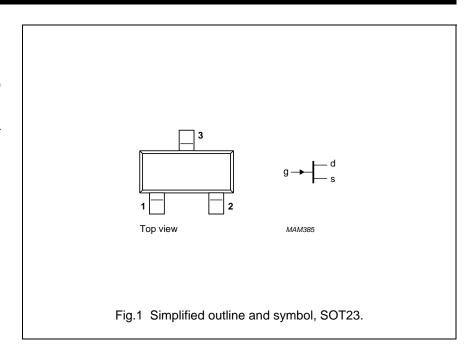
1. Drain and source are interchangeable.

Marking code

PMBF4391 = p6J

PMBF4392 = p6K

PMBF4393 = p6G



QUICK REFERENCE DATA

		PMBF4391		PMBF4392 PMBF4		F4393
Drain-source voltage	$\pm \ V_{DS}$	max.	40	40	40	V
Drain current						
$V_{DS} = 20 \text{ V}; V_{GS} = 0$	I_{DSS}	>	50	25	5	mA
Gate-source cut-off voltage						
$V_{DS} = 20 \text{ V; } I_D = 1 \text{ nA}$	-V _{(P)GS}	>	4	2	0.5	V
VDS = 20 V, ID = 1 IIA	−v(P)GS	<	10	5	3	V
Drain-source resistance (on) at f = 1 kHz						
$I_D = 0; V_{GS} = 0$	$R_{ds on}$	<	30	60	100	Ω
Feedback capacitance at f = 1 MHz						
$-V_{GS} = 12 \text{ V}; V_{DS} = 0$	C_{rs}	<	3.5	3.5	3.5	pF
Turn-off time						
$V_{DD} = 10 \text{ V}; V_{GS} = 0$						
$I_D = 12 \text{ mA}; -V_{GSM} = 12 \text{ V}$	t_{off}	<	20	_	_	ns
$I_D = 6 \text{ mA}; -V_{GSM} = 7 \text{ V}$	t_{off}	<	_	35	_	ns
$I_D = 3 \text{ mA}; -V_{GSM} = 5 \text{ V}$	t_{off}	<	_	_	50	ns

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RATINGS								
	ccordance with the Absolute Max	kimum Svstem (IEC 13	34)				
Drain-source volta				√ _{DS}	max.	40	V	
Drain-gate voltage			± vbs V _{DGO}		max.	40		
Gate-source voltage				'GSO	max.	40		
Gate current (DC)	,-		I _G	G 50	max.		mA	
Total power dissipation up to $T_{amb} = 40 ^{\circ}\text{C}^{(1)}$			P _{tot}		max.		mW	
Storage temperatu					-65 to + 150			
Junction temperatu	•		T _{stg} T _j			150		
THERMAL RESIST	ANCE							
From junction to a	mbient ⁽¹⁾		Rt	h j-a	=	430	K/W	
CHARACTERISTIC								
$T_j = 25 ^{\circ}\text{C} \text{ unless of}$								
Gate-source voltag								
$I_G = 1 \text{ mA}; V_{DS} =$				V_{GSon}	<		1	V
Gate-source cut-of								
$V_{DS} = 0 \text{ V}; -V_{GS} = 20 \text{ V}$				-I _{GSS}	<		0.1	nA
$V_{DS} = 0 \text{ V}; -V_{GS} = 20 \text{ V}; T_{amb} = 150 ^{\circ}\text{C}$				$-I_{GSS}$	< I	1	0.2	μΑ
			PME	3F4391	PMBF43	92	PMRF	F4393
			1 1411	JI 400 I	1 10101 40	32		
Drain current		I _{DSS}	>	50	1 11151 40	25	5	mA
Drain current V _{DS} = 20 V; V _{GS}	= 0	I _{DSS}			1 11151 40			
		I _{DSS}	>	50	T INDI 40	25	5	mA
$V_{DS} = 20 \text{ V}; V_{GS}$	down voltage	I _{DSS} -V _{(BR)GSS}	>	50	T MIST 40	25	5	mA
$V_{DS} = 20 \text{ V}; V_{GS}$ Gate-source break	down voltage = 0		> <	50 150	1 11151 40	25 75	5 30 40 0.5	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS}	down voltage = 0 f voltage	−V _(BR) GSS	> <	50 150	T IIISI 40	25 75 40	5 30 40	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-of	down voltage = 0 f voltage 20 V	−V _(BR) GSS	> < < > >	50 150 40 4	T IIISI 40	25 75 40 2	5 30 40 0.5	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-of I_D = 1 nA; V_{DS} =	down voltage = 0 f voltage 20 V ge (on)	−V _(BR) GSS	> < < > >	50 150 40 4	T III ST 40	25 75 40 2	5 30 40 0.5	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-of I_D = 1 n A; V_{DS} = Drain-source voltage	down voltage = 0 f voltage 20 V ge (on) = 0	−V _{(BR)GSS} −V _{(P)GS}	> <	50 150 40 4 10	T III ST 40	25 75 40 2	5 30 40 0.5	mA mA V V
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-of I_D = 1 n A; V_{DS} = Drain-source voltat I_D = 12 m A; V_{GS}	down voltage = 0 f voltage 20 V ge (on) = 0	$-V_{(BR)GSS}$ $-V_{(P)GS}$ V_{DSon}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10	T III ST 40	25 75 40 2 5	5 30 40 0.5 3	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-of I_D = 1 nA; V_{DS} = Drain-source voltage I_D = 12 mA; V_{GS} = I_D = 6 mA; V_{GS} =	down voltage = 0 f voltage 20 V ge (on) = 0 = 0	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10	T III ST 40	25 75 40 2 5	5 30 40 0.5 3	mA mA V V V
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-of I_D = 1 nA; V_{DS} = Drain-source voltage I_D = 12 mA; V_{GS} = I_D = 6 mA; V_{GS} = I_D = 3 mA; V_{GS} = Drain-source resist	down voltage = 0 f voltage 20 V ge (on) = 0 = 0	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10		25 75 40 2 5	5 30 40 0.5 3	mA mA V V V
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-of I_D = 1 nA; V_{DS} = Drain-source voltage I_D = 12 mA; V_{GS} = I_D = 6 mA; V_{GS} = I_D = 3 mA; V_{GS} = Drain-source resist	down voltage = 0 f voltage 20 V ge (on) = 0 = 0 = 0 tance (on) = 1 kHz; T _{amb} = 25 °C	-V _{(BR)GSS} -V _{(P)GS} V _{DSon} V _{DSon} V _{DSon}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10 0.4		25 75 40 2 5	5 30 40 0.5 3	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-of I_D = 1 n A; V_{DS} = Drain-source voltat I_D = 12 m A; V_{GS} = I_D = 6 m A; V_{GS} = I_D = 3 m A; V_{GS} = Drain-source resis: I_D = 0; V_{GS} = 0;	down voltage = 0 f voltage 20 V ge (on) = 0 = 0 = 0 tance (on) = 1 kHz; T _{amb} = 25 °C	-V _{(BR)GSS} -V _{(P)GS} V _{DSon} V _{DSon} V _{DSon}	> < < > < < < < < < < < < < < < < < < <	50 150 40 4 10 0.4		25 75 40 2 5	5 30 40 0.5 3	mA mA
V_{DS} = 20 V; V_{GS} Gate-source break $-I_G$ = 1 μ A; V_{DS} Gate-source cut-of I_D = 1 nA; V_{DS} = Drain-source voltat I_D = 12 mA; V_{GS} = I_D = 6 mA; V_{GS} = I_D = 3 mA; V_{GS} = Drain-source resis: I_D = 0; V_{GS} = 0; V_{CS}	down voltage = 0 f voltage 20 V ge (on) = 0 = 0 = 0 tance (on) = 1 kHz; T _{amb} = 25 °C	-V _{(BR)GSS} -V _{(P)GS} V _{DSon} V _{DSon} V _{DSon} r _{ds on}	> <	50 150 40 4 10 0.4 -		25 75 40 2 5	5 30 40 0.5 3	mA mA V V V V
$V_{DS} = 20 \text{ V}; V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A}; V_{DS}$ $Gate\text{-source cut-of}$ $I_D = 1 \text{ nA}; V_{DS} = 1 \text{ Drain-source voltan}$ $I_D = 12 \text{ mA}; V_{GS} = 1 In mathematical mathem$	down voltage = 0 f voltage 20 V ge (on) = 0 = 0 = 0 tance (on) = 1 kHz; T _{amb} = 25 °C ot V _{DS} = 20 V	-V _{(BR)GSS} -V _{(P)GS} V _{DSon} V _{DSon} V _{DSon} r _{ds on}	>	50 150 40 4 10 0.4 -		25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100	mA mA V V V V V
$V_{DS} = 20 \text{ V; } V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A; } V_{DS}$ $Gate\text{-source cut-of}$ $I_D = 1 \text{ nA; } V_{DS} = 1000 \text{ mA; } V_{GS} = 10000 \text{ mA; } V_{GS} = 1000 \text{ mA; } V_{GS} = 1$	down voltage = 0 f voltage 20 V ge (on) = 0 = 0 = 0 tance (on) = 1 kHz; T _{amb} = 25 °C	-V _(BR) GSS -V _(P) GS V _{DSon} V _{DSon} V _{DSon} r _{ds on} I _{DSX} I _{DSX}	>	50 150 40 4 10 0.4 - 30 0.1 -		25 75 40 2 5 - 0.4 -	5 30 40 0.5 3	mA mA V V V V V V
$V_{DS} = 20 \text{ V}; V_{GS}$ $Gate\text{-source break}$ $-I_G = 1 \mu\text{A}; V_{DS}$ $Gate\text{-source cut-of}$ $I_D = 1 \text{ nA}; V_{DS} = 1 \text{ Drain-source voltan}$ $I_D = 12 \text{ mA}; V_{GS} = 1 In mathematical mathem$	down voltage = 0 f voltage 20 V ge (on) = 0 = 0 = 0 tance (on) = 1 kHz; T _{amb} = 25 °C ot V _{DS} = 20 V	-V _{(BR)GSS} -V _{(P)GS} V _{DSon} V _{DSon} V _{DSon} I _{DSX} I _{DSX} I _{DSX}	>	50 150 40 4 10 0.4 - 30 0.1 -		25 75 40 2 5 - 0.4 -	5 30 40 0.5 3 - - 0.4 100 - - 0.1	mA mA V V V V V V T Ω

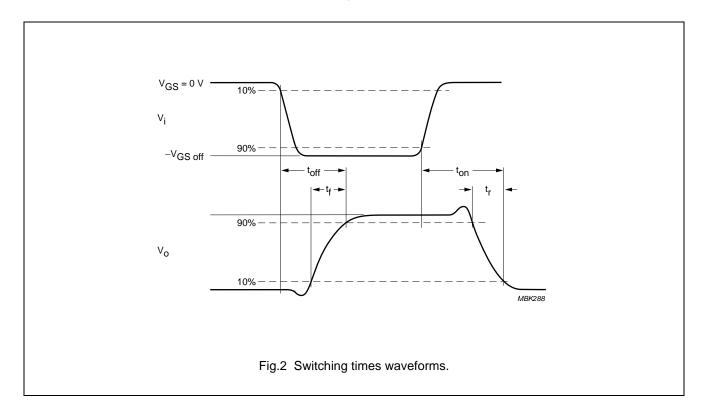
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y-parameters (common source)						
V_{DS} = 20 V; V_{GS} = 0; f = 1 MHz; T_{amb} = 25 °C			F4391	PMBF4392	PMBF4393	
Input capacitance	C_{is}	<	14	14	14	pF
Feedback capacitance						
$-V_{GS} = 12 \text{ V}$; $V_{DS} = 0$	C_{rs}	<	3.5	_	_	pF
$-V_{GS} = 7 V$; $V_{DS} = 0$	C_{rs}	<	_	3.5	_	pF
$-V_{GS} = 5 V$; $V_{DS} = 0$	C_{rs}	<	_	_	3.5	pF
Switching times						
$V_{DD} = 10 \text{ V}$; $V_{DS} = 0$						
Conditions I _D and -V _{GSoff}	I_D	=	12	6	3	mA
	$-V_{GS\ off}$	=	12	7	5	V
	R_L	=	750	1550	3150	Ω
Rise time	t _r	<	5	5	5	ns
Turn on time	t _{on}	<	15	15	15	ns
Fall time	t _f	<	15	20	30	ns
Turn off time	t_{off}	<	20	35	50	ns

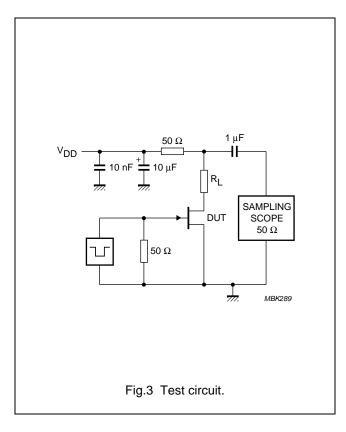
Note

1. Mounted on a ceramic substrate of 8 mm \times 10 mm \times 0,7 mm.



N-channel FETs

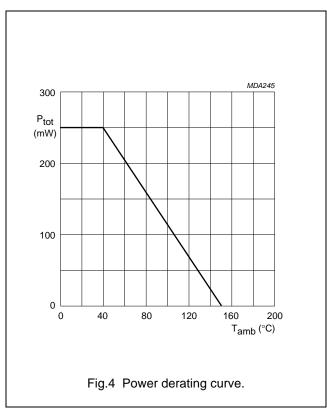
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Pulse generator:

 $\begin{array}{llll} t_r & < & 0.5 & \text{ns} \\ t_f & < & 0.5 & \text{ns} \\ t_p & = & 100 & \mu \text{s} \\ \delta & = & 0.01 & \\ \\ \text{Oscilloscope:} \end{array}$

 $R_i = 50 \Omega$



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PACKAGE OUTLINE

mm

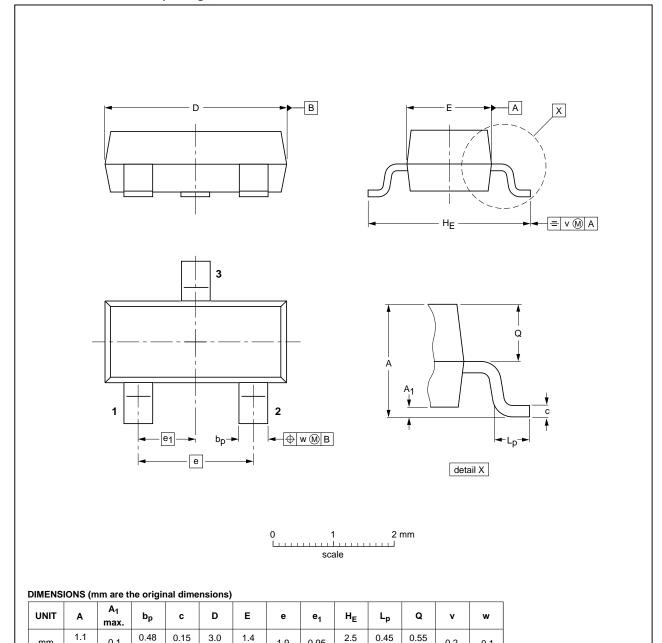
0.1

0.38

0.9

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT23		TO-236AB				-04-11-04 06-03-16

0.2

0.1

0.95

1.9

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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